

## Preliminary Data Sheet

LED Chip Infrared

YL-C760nM-35mW(N)

Rev. 05, 2017

Radiation	Type	Electrodes
Infrared	AlGaAs/AlGaAs, DDH	N (cathode) up

	<p>typ. dimensions (<math>\mu\text{m}</math>)</p> <p>typ. thickness: <math>150 \pm 30 \mu\text{m}</math></p> <p>cathode: gold alloy</p> <p>anode: gold alloy</p>
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### Optical and Electrical Characteristics

$T_{\text{amb}} = 25^\circ\text{C}$ , unless otherwise specified

Parameter	Test cond.	Symbol	Min	Typ	Max	Unit
Forward voltage	$I_F = 100 \text{ mA}$	$V_F$		1.65	1.9	V
Forward voltage	$I_F = 350 \text{ mA}$	$V_F$		1.85	2.05	V
Reverse current	$V_R = 5 \text{ V}$	$I_R$			10	$\mu\text{A}$
Radiant power*	$I_F = 50 \text{ mA}$	$\Phi_e$	5.6	7		mW
Radiant power*	$I_F = 350 \text{ mA}$	$\Phi_e$		35		mW
Peak wavelength	$I_F = 100 \text{ mA}$	$\lambda_p$	750	760	770	nm
FWHM	$I_F = 350 \text{ mA}$	$\Delta\lambda_{0.5}$		27		nm
Switching time	$I_F = 100 \text{ mA}$	$t_r, t_f$		40		ns

\*Measured on bare chip on TO-18 header

### Packing

Chips on adhesive film with wire bond side up

Art. No. 113 056



We reserve the right to make changes to improve technical design and may do so without further notice. Parameters can vary in different applications. All operating parameters must be validated for each customer application by the customer.